2SA2140

Silicon PNP epitaxial planar type

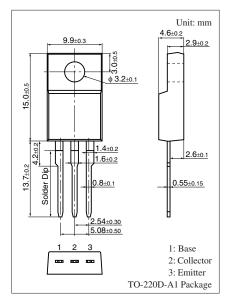
For power amplification For TV VM circuit

■ Features

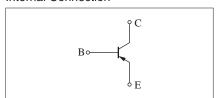
- Satisfactory linearity of forward current transfer ratio h_{FE}
- High transition frequency (f_T)
- Full-pack package which can be installed to the heat sink with one screw.

■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emit	V_{CBO}	-180	V	
Collector-emitter voltage (B	V_{CEO}	-180	V	
Emitter-base voltage (Collec	V_{EBO}	-6	V	
Collector current	I_C	-1.5	A	
Peak collector current	I_{CP}	-3	A	
Collector power dissipation	P_{C}	20	W	
Г	$\Gamma_{\rm a} = 25^{\circ}{\rm C}$		2.0	
Junction temperature		T_{j}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C



Internal Connection



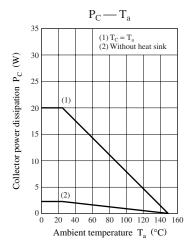
■ Electrical Characteristics $T_C = 25$ °C ± 3 °C

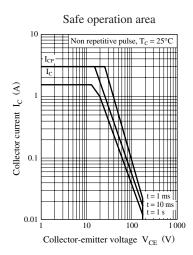
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-180			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -180 \text{ V}, I_E = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -6 \text{ V}, I_C = 0$			-100	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = -5 \text{ V}, I_{C} = -0.1 \text{ A}$	60		240	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -1 A, I_B = -0.1 A$			- 0.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -0.2 \text{ A}, f = 10 \text{ MHz}$		100		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		30		pF
(Common base, input open circuited)						
Turn-on time	t _{on}	$I_C = -0.4$ A, Resistance loaded		0.1		μs
Storage time	t _{stg}	$I_{B1} = 0.04 \text{ A}, I_{B2} = -0.04 \text{ A}$		1.0		μs
Fall time	t _f	$V_{CC} = 100 \text{ V}$		0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	Р		
h_{FE}	60 to 140	120 to 240		





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